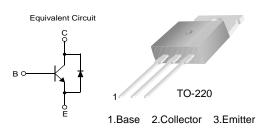


High Voltage High Speed Power Switch Application

- Wide Safe Operating Area
- Built-in Free Wheeling diodeSuitable for Electronic Ballast Application
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time



Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	700	V	
V _{CEO}	Collector-Emitter Voltage	400	V	
V _{EBO}	Emitter-Base Voltage	12	V	
I _C	Collector Current (DC)	4	А	
I _{CP}	* Collector Current (Pulse)	8	A	
I _B	Base Current (DC)	2	А	
I _{BP}	* Base Current (Pulse)	4	А	
P _C	Collector Dissipation (T _C =25°C)	70	W	
T _{STG}	Storage Temperature	- 65 ~ 150	°C	

* Pulse Test Pulse Width = 5ms, Duty Cycle $\geq 1.0\%$

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1mA, I_{E} = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 5 {\rm mA}, \ I_{\rm B} = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 1mA, I_{C} = 0$	12			V
I _{CES}	Collector Cut-off Current	$V_{CE} = 700V, V_{EB} = 0$			100	mA
I _{CEO}	Collector Cut-off Current	V _{CE} = 400V, IB = 0			250	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 12V, I_{C} = 0$			100	mA

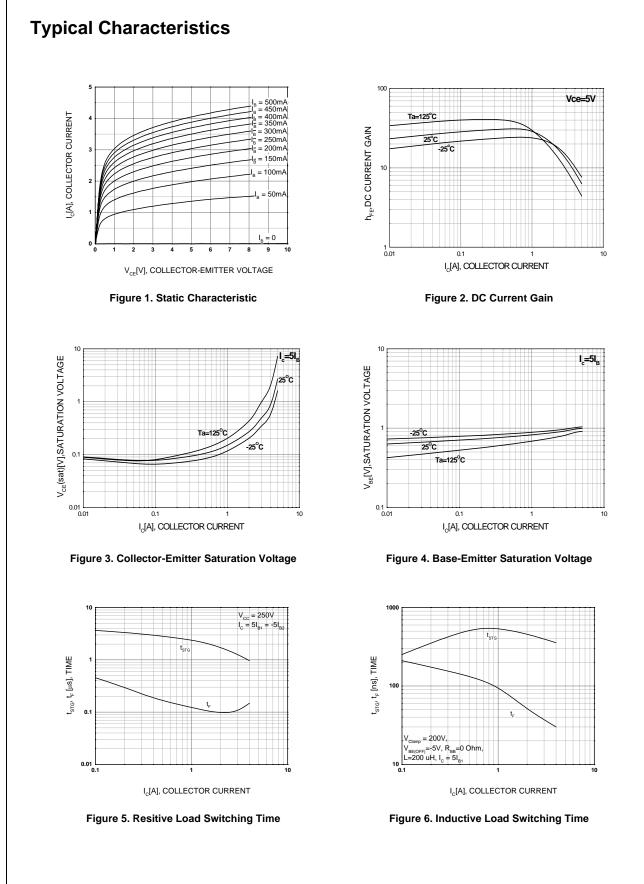
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h _{FE}	DC Current Gain		10 8		40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 0.5A, I_{B} = 0.1A$ $I_{C} = 1A, I_{B} = 0.2A$ $I_{C} = 2.5A, I_{B} = 0.5A$			0.7 1.0 1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$\begin{split} I_{C} &= 0.5A, \ I_{B} = 0.1A \\ I_{C} &= 1A, \ I_{B} = 0.2A \\ I_{C} &= 2.5A, \ I_{B} = 0.5A \end{split}$			1.1 1.2 1.3	V
V _f	Internal Diode Forward Voltage Drop	I _F = 2A			2.5	V
Inductive Lo	oad Switching (V _{CC} = 200V)					
t _{stg}	Storage Time	I _C = 2A, I _{B1} = 0.4A		0.6		μS
tf	Fall Time	$V_{BE}(off) = -5V, L = 200\mu H$		0.1		
Resistive L	oad Switching (V _{CC} = 250V)			•		
t _{stg}	Storage Time	$I_{\rm C} = 2A, \ I_{\rm B1} = I_{\rm B2} = 0.4A$			2.9	μS
tf	Fall Time	T _P = 30μs		0.2		

* Pulse test: PW \leq 300 μ s, Duty cycle \leq 2%

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.78	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	62.5	°C/W



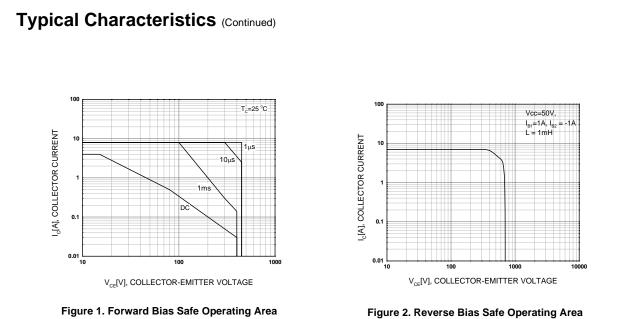
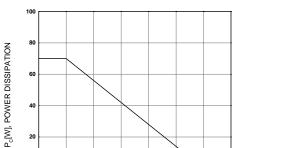


Figure 1. Forward Bias Safe Operating Area



100 T_c[°C], CASE TEMPERATURE

125

150 175

Figure 3. Power Derating

FJP5304D — NPN Silicon Transistor

0 L 0

25

50 75



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